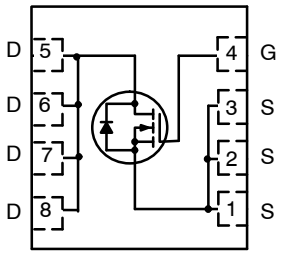
MOSFET – N-Channel, UltraFET Trench

200 V, 9.5 A, 200 mΩ

FDMC2610

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
200 V	200 mΩ @ 10 V	9.5 A
	215 mΩ @ 6 V	



N-CHANNEL MOSFET

General Description

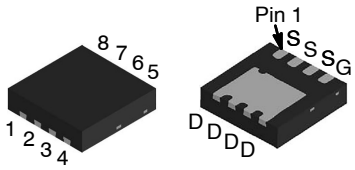
This N−Channel MOSFET is a rugged gate version of **onsemi**'s advanced POWERTRENCH® process. It has been optimized for power management applications.

Features

- Max $R_{DS(on)}$ = 200 mΩ at V_{GS} = 10 V, I_D = 2.2 A
- Max $R_{DS(on)}$ = 215 mΩ at V_{GS} = 6 V, I_D = 1.5 A
- Low Profile − 1 mm Max in a Power 33
- Pb−Free, Halide Free and RoHS Compliant

Applications

- DC−DC Conversion



WDFN8 3.3 × 3.3, 0.65P
CASE 511DH

MOSFET MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

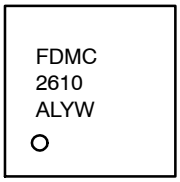
Symbol	Parameter	Value	Unit
V_{DS}	Drain to Source Voltage	200	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current: Continuous (Silicon limited) T_C = 25°C Continuous (Note 1a) T_A = 25°C Pulsed	 9.5 2.2 15	A
E_{AS}	Single Pulse Avalanche Energy (Note 3)	6	mJ
P_D	Power Dissipation: T_C = 25°C T_A = 25°C (Note 1a)	 42 2.1	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	60	

MARKING DIAGRAM



FDMC2610 = Specific Device Code
A = Assembly Site
L = Wafer Lot Number
YW = Assembly Start Week

ORDERING INFORMATION

Device	Package	Shipping†
FDMC2610	WDFN8 (Pb−Free, Halide Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

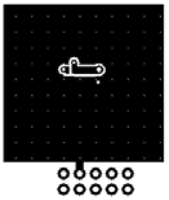
ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	200	–	–	V
ΔBV_{DSS} /ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C	–	199	–	mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 160 V, V_{GS} = 0 V	–	–	1	μA
		V_{DS} = 160 V, V_{GS} = 0 V, T_J = 125°C	–	–	100	
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	–	–	±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2	3.2	4	V
$\Delta V_{GS(th)}$ /ΔT_J	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C	–	–9.9	–	mV/°C
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 10 V, I_D = 2.2 A	–	175	200	mΩ
		V_{GS} = 6 V, I_D = 1.5 A,	–	188	215	
		V_{GS} = 10 V, I_D = 2.2 A, T_J = 125°C	–	347	397	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 2.2 A	–	7	–	S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 100 V, V_{GS} = 0 V, f = 1 MHz	–	720	960	pF
C_{oss}	Output Capacitance		–	41	55	pF
C_{rss}	Reverse Transfer Capacitance		–	12	20	pF
R_g	Gate Resistance	f = 1 MHz	–	0.7	–	Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 100 V, I_D = 2.2 A, V_{GS} = 10 V, R_{GEN} = 24 Ω	–	17	31	ns
t_r	Rise Time		–	13	24	ns
$t_{d(off)}$	Turn-Off Delay Time		–	29	47	ns
t_f	Fall Time		–	16	29	ns
$Q_{g(TOT)}$	Total Gate Charge at 10 V	V_{GS} = 0 V to 10 V, V_{DD} = 100 V, I_D = 2.2 A	–	12.3	18	nC
Q_{gs}	Gate to Source Gate Charge	V_{DD} = 100 V, I_D = 2.2A	–	3	–	nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 100 V, I_D = 2.2 A	–	3.6	–	nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 2.2 A (Note 2)	–	0.8	1.2	V
t_{rr}	Reverse Recovery Time	I_F = 2.2 A, di/dt = 100 A/μs	–	69	104	ns
Q_{rr}	Reverse Recovery Charge		–	114	171	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 oz copper pad on a 1.5 × 1.5 in. board of FR−4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user’s board design.



a) 60°C/W when mounted on a 1 in^2 pad of 2 oz copper.

b) 135°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. Starting T_J = 25°C; N-ch: L = 3 mH, I_{AS} = 2 A, V_{DD} = 200 V, V_{GS} = 10 V.

TYPICAL CHARACTERISTICS

(T_J = 25°C unless otherwise noted)

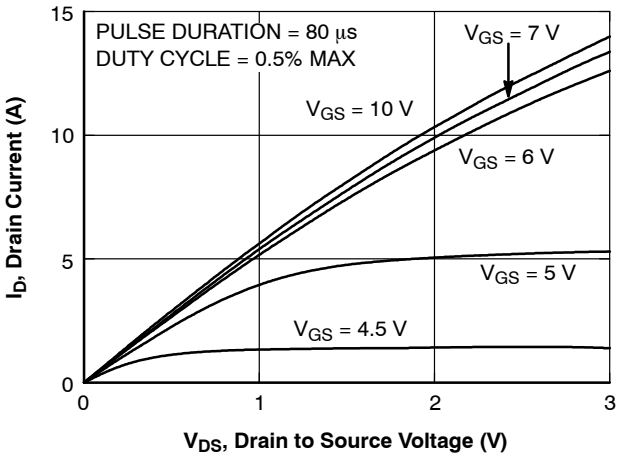


Figure 1. On−Region Characteristics

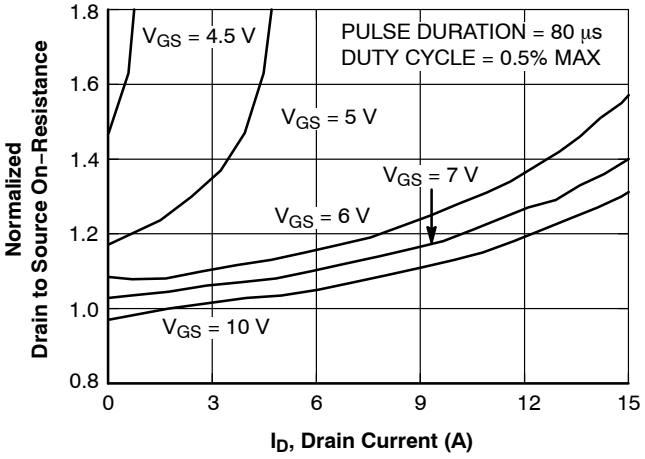


Figure 2. Normalized On−Resistance vs. Drain Current and Gate Voltage

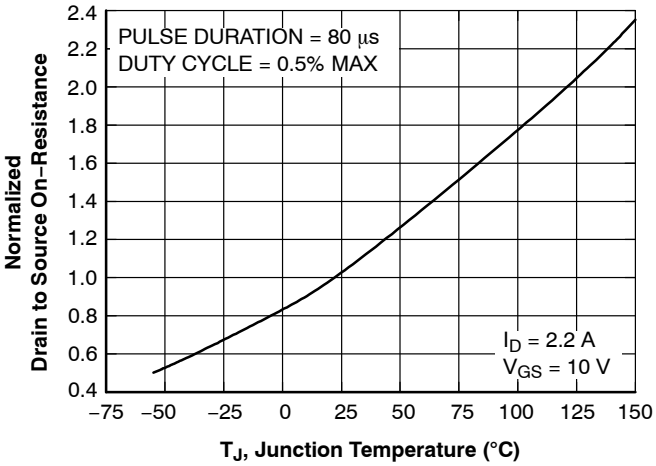


Figure 3. Normalized On−Resistance vs. Junction Temperature

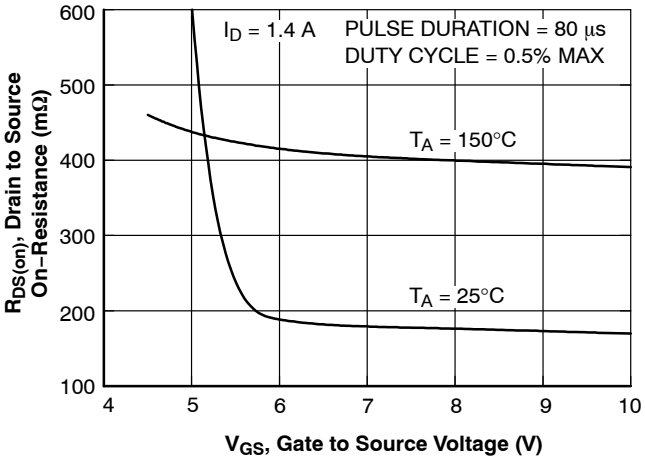


Figure 4. On−Resistance vs. Gate to Source Voltage

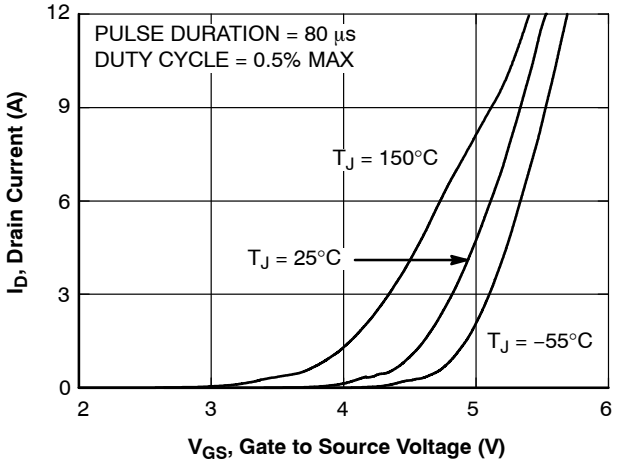


Figure 5. Transfer Characteristics

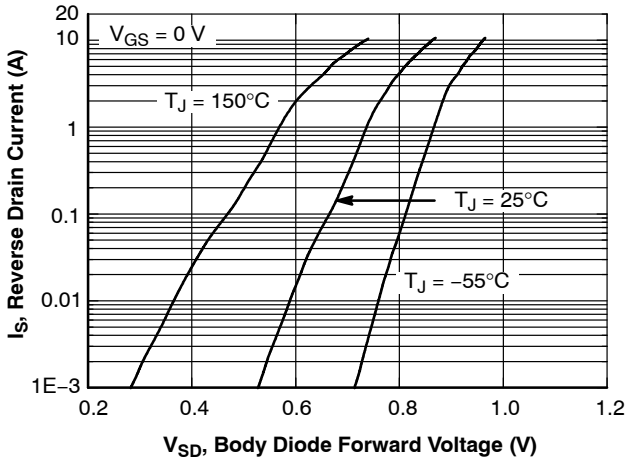


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (continued)

(T_J = 25°C unless otherwise noted)

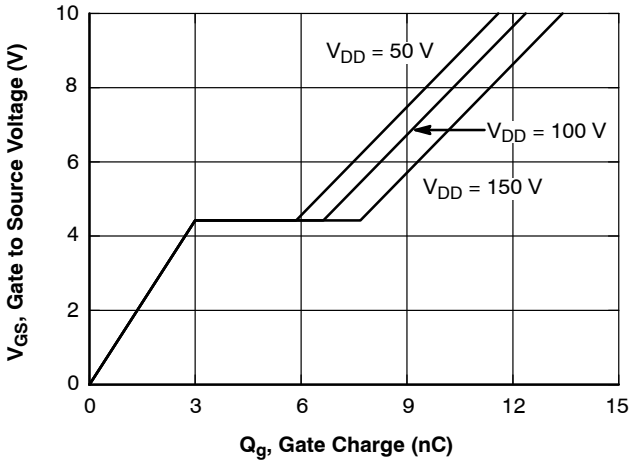


Figure 7. Gate Charge Characteristics

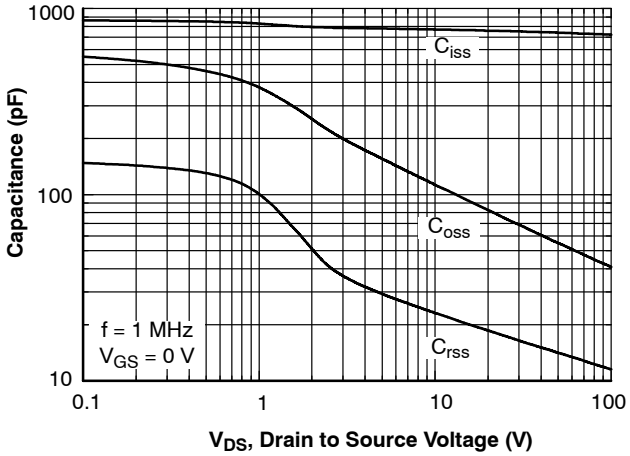


Figure 8. Capacitance vs. Drain to Source Voltage

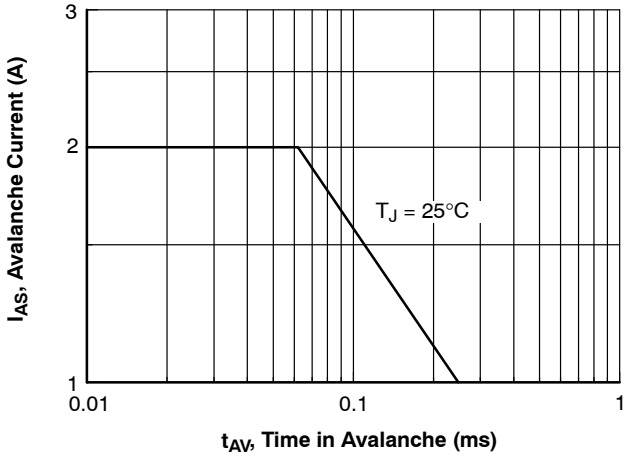


Figure 9. Unclamped Inductive Switching Capability

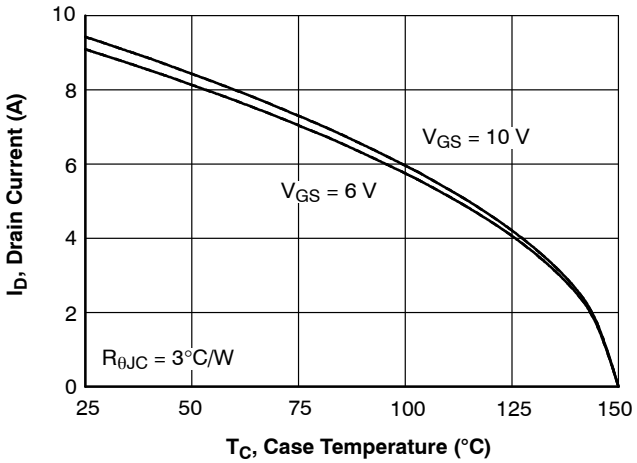


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

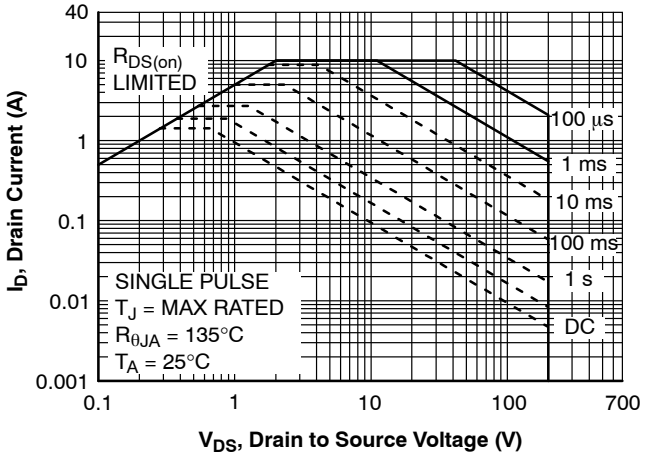


Figure 11. Forward Bias Safe Operating Area

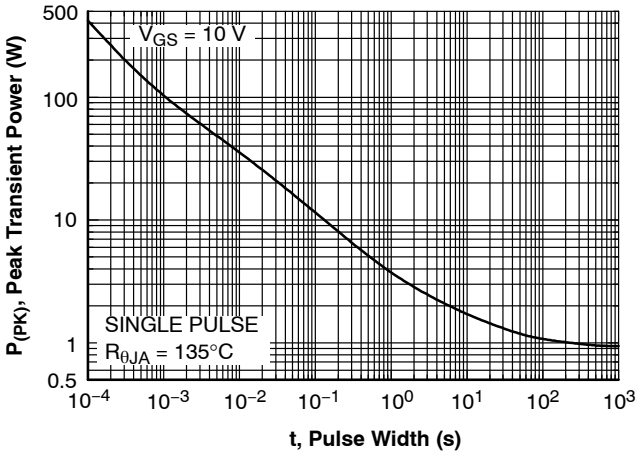


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (continued)

(T_J = 25°C unless otherwise noted)

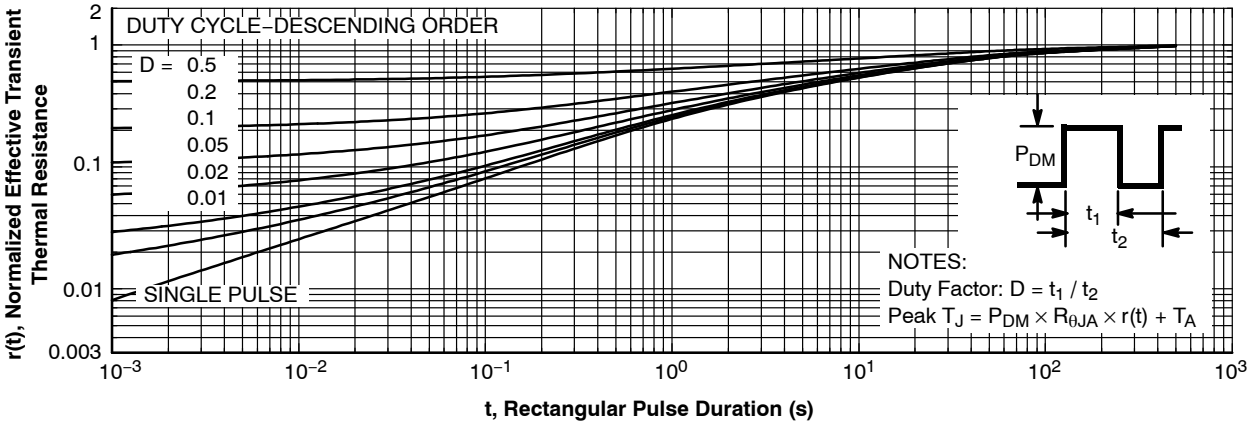
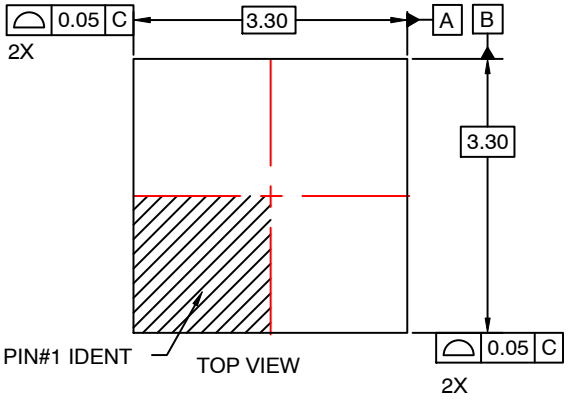
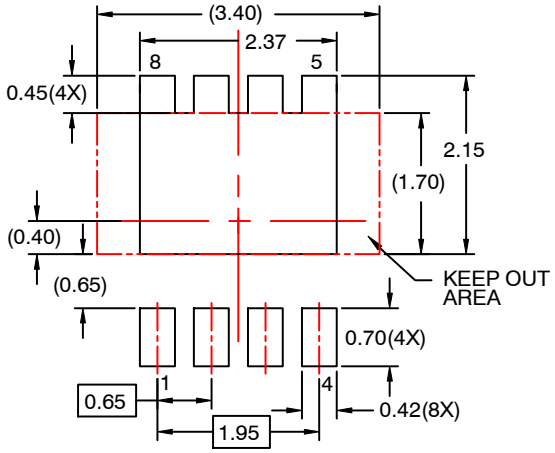


Figure 13. Transient Thermal Response Curve

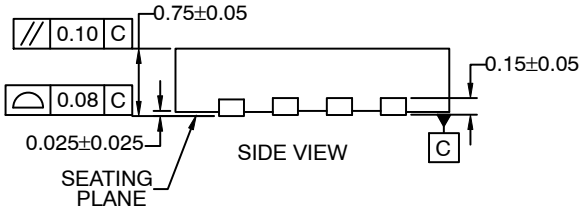
WDFN8 3.3x3.3, 0.65P
CASE 511DH
ISSUE O

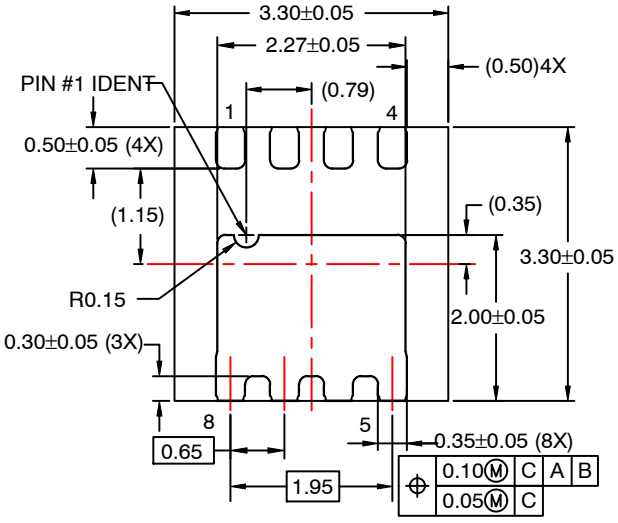
DATE 31 JUL 2016





RECOMMENDED LAND PATTERN





BOTTOM VIEW

NOTES:

A. DOES NOT CONFORM TO JEDEC REGISTRATION MO−229

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.

D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

DOCUMENT NUMBER:	**98AON13625G**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**WDFN8 3.3X3.3, 0.65P**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales